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1. (Once Amended) A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film; and

depositing Al-Si-Cu film on the Ti film at a temperature of at least 400 °C to form a layer of Al_3Ti , which prevents Si-recrystallization in a subsequent cooling process.

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2. (Once Amended) A method of depositing a wiring thin film on a semiconductor substrate, comprising the steps of:

depositing a Ti film; and

depositing Al-Si-Cu film on the Ti film; and

annealing the semiconductor substrate at a temperature of at least 400 °C to form a layer of Al_3Ti , which prevents Si-recrystallization in a subsequent cooling process.

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(2). Please add the following claims:

8. (Newly Added) A method as recited in claim 1, further comprising, after said forming said layer of AlTi_3 , patterning an Al layer.

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9. (Newly Added) A method as recited in claim 2, after said forming said layer of AlTi_3 , patterning an Al layer.